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ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Vertical-Stacked-Array-Transistor (VSAT) for Nonvolatile Memory Devices
- Magnetic Memory Bits with Perpendicular Magnetization Switched By Current-Induced Spin-Orbit Torques
- Vsat Structure for Nonvolatile Memory Device
- A Read-Disturbance-Free Nonvolatile Content Adressable Memory
- A Self-Organized Critical CMOS Circuit for Computation and Information Processing
- Anti-Ferromagnetic Magneto-Electric Spin-Orbit Read Logic

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